

Weak-localization corrections to the conductivity of double quantum wells

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Abstract

The weak-localization contribution $\delta\sigma(B)$ to the conductivity of a tunnel-coupled double-layer electron system is evaluated and its behavior in weak magnetic fields B perpendicular or parallel to the layers is examined. In a perpendicular field B , $\delta\sigma(B)$ increases and stays dependent on tunneling as long as the magnetic field is smaller than $\hbar/eD\tau_t$, where D is the in-plane diffusion coefficient and τ_t the interlayer tunneling time. If τ_t is smaller than the inelastic scattering time, a parallel magnetic field also leads to a considerable increase of the conductivity starting with a B^2 law and saturating at fields higher than $\hbar/eZ\sqrt{D\tau_t}$, where Z is the interlayer distance. In the limit of coherent tunneling, when τ_t is comparable to elastic scattering time, $\delta\sigma(B)$ differs from that of a single-layer system due to ensuing modifications of the diffusion coefficient. A possibility to probe the weak-localization effect in double-layer systems by the dependence of the conductivity on the gate-controlled level splitting is discussed.

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I. INTRODUCTION

The interference of electronic waves leads to negative corrections to the conductivity of electron systems. This effect is known as weak localization. It can be observed at very low temperatures, when the inelastic scattering rate is so small that the phase coherence is kept over many acts of elastic scattering. Although these quantum corrections are usually small, they can be distinguished due to their specific dependence on temperature, magnetic field, and frequency of the applied electric field.

The fundamentals of the theory of weak localization have been developed in Refs. 1-4 and a review is given in Ref. 5. Recently considerable attention⁶⁻¹⁶ has been drawn to weak-localization phenomena in layered systems where characteristic features are caused by a dimensionality crossover. These studies have been applied mostly to multilayer systems (superlattices) although the cases of barrier-separated thin metallic films^{9,10} and single-barrier structures¹² have also been investigated. In this paper we calculate the weak-localization corrections to the in-plane conductivity of two tunnel-coupled two-dimensional (2D) layers, the system which is typically formed in double quantum well structures¹⁷. Such double-layer electron systems represent an intermediate case between a single 2D layer and a three-dimensional superlattice and their various interesting properties are caused mainly by this fact. As concerns the weak localization problem, the tunnel coupling introduces an additional cutoff parameter in the diffusion pole, which implies that the weak-localization contribution to the conductivity depends on the strength of this coupling. This happens when the probability of tunneling is not small in comparison to that of inelastic scattering. Another important consequence of the tunnel coupling is that a weak magnetic field B applied *parallel* to the layers leads to a delocalization as does a field B applied *perpendicular* to the layers⁴. The physical origin of the effect of parallel field is explained in a similar way: this field introduces an additional phase for the electron which moves in one layer, then tunnels into another layer, moves there, and finally tunnels back and returns to the initial point. The described phenomena are the subject of the present study.

The paper is organized as follows. In Sec. II we present the basic formalism for the calculation of the weak-localization contribution to the conductivity of a double-layer system. In Sec. III we calculate the magnetoconductivity in a *perpendicular* magnetic field B and in Sec. IV we repeat the calculation for a *parallel* field B . In Sec. V we study the magnetoconductivity in conditions of coherent tunnel coupling, when the tunneling probability is comparable to or greater than the probability of elastic scattering. In Sec. VI we discuss the results and consider the possibility to probe the weak-localization effects in double quantum wells by examining the dependence of the conductivity on the gate-controlled energy splitting of the lowest two levels of the double quantum well.

II. FORMALISM

The Hamiltonian of the double quantum well system is given, in the basis of the left (l) and right (r) layer orbitals $|l\rangle$ and $|r\rangle$, by

$$\hat{H}(\mathbf{x}) = \hat{P}_l [E_l(\mathbf{x}) + V_l(\mathbf{x})] + \hat{P}_r [E_r(\mathbf{x}) + V_r(\mathbf{x})] + \hat{h} \quad (1)$$

where $\mathbf{x} = (x, y)$ is the in-plane position vector; $E_j(\mathbf{x}) = \langle j | (-i\hbar\partial/\partial\mathbf{x} + e\mathbf{A}(\mathbf{x}, z))^2 | j \rangle / 2m$ ($j = l, r$) is the matrix element of the kinetic energy operator, $\mathbf{A}(\mathbf{x}, z)$ the vector-potential, e the elementary charge, m the effective mass, and $V_j(\mathbf{x}) = \langle j | V(\mathbf{x}, z) | j \rangle$ the matrix element of the disorder potential. Further,

$$\hat{h} = \frac{\Delta}{2} \hat{\sigma}_z + T \hat{\sigma}_x, \quad (2)$$

is the potential energy matrix of the double quantum well system expressed through the energy level splitting Δ and tunneling matrix element T . Finally, $\hat{\sigma}_i$ are the Pauli matrices and $\hat{P}_l = (1 + \hat{\sigma}_z)/2$ and $\hat{P}_r = (1 - \hat{\sigma}_z)/2$ the projection matrices.

According to the Kubo formula, the zero-temperature dc conductivity is given by

$$\sigma_{\alpha\alpha'} = \frac{e^2\hbar}{2\pi m^2 L^2} \sum_{bb'=R,A} (-1)^l \text{Tr} \int \int d\mathbf{x} d\mathbf{x}' \langle \hat{\pi}^\alpha(\mathbf{x}) \hat{G}_{E_F}^b(\mathbf{x}, \mathbf{x}') \hat{\pi}^{\alpha'}(\mathbf{x}') \hat{G}_{E_F}^{b'}(\mathbf{x}', \mathbf{x}) \rangle \quad (3)$$

where $\hat{G}_{E_F}^{R,A}(\mathbf{x}, \mathbf{x}')$ are the Green's functions of the electron system with Fermi energy E_F , L^2 is the normalization area, $\hat{\pi}^\alpha(\mathbf{x})$ is the kinematic momentum operator, whose matrix elements are given as $[\hat{\pi}(\mathbf{x})]_{jj} = \langle j | -i\hbar\partial/\partial\mathbf{x} + e\mathbf{A}(\mathbf{x}, z) | j \rangle$, and α and α' are the coordinate indices (x, y) . The angular brackets $\langle \dots \rangle$ denote statistical averaging, Tr denotes the trace, and $l = 1$ for $b = b'$ and $l = 0$ for $b \neq b'$.

The weak-localization contribution $\delta\sigma_{\alpha\alpha'}$ to the in-plane conductivity is given by the sum of an infinite set of diagrams with two or more maximally crossed impurity lines. Below we consider a system of randomly distributed elastic scatterers (impurities) described by the correlation function $\langle V_j(\mathbf{x})V_{j'}(\mathbf{x}') \rangle = W_{jj'}(\mathbf{x}, \mathbf{x}') = w_j\delta_{jj'}\delta(\mathbf{x} - \mathbf{x}')$. We obtain

$$\delta\sigma_{\alpha\alpha'} = \frac{e^2\hbar}{2\pi m^2 L^2} \sum_{bb'=R,A} (-1)^l \sum_{jj'j_1j_2} \int \int d\mathbf{x}d\mathbf{x}' \pi_{jj}^\alpha(\mathbf{x}) G_{jj_1}^b(\mathbf{x}, \mathbf{x}_1) G_{jj_2'}^b(\mathbf{x}_2, \mathbf{x}') \\ \times \pi_{j'j'}^{\alpha'}(\mathbf{x}') G_{j'j_1}^{b'}(\mathbf{x}', \mathbf{x}_1) G_{j_2j}^{b'}(\mathbf{x}_2, \mathbf{x}) \tilde{C}_{j_1j_2}^{bb'}(\mathbf{x}_1, \mathbf{x}_2), \quad (4)$$

where $G_{jj'}^b(\mathbf{x}, \mathbf{x}') = \langle [\hat{G}_{E_F}^b(\mathbf{x}, \mathbf{x}')]_{jj'} \rangle$ are the averaged one-particle Green's functions, and $\tilde{C}_{j_1j_2}^{bb'}(\mathbf{x}_1, \mathbf{x}_2)$ is the Cooperon, the solution of the Bethe-Salpeter equation, given by

$$\tilde{C}_{j_1j_2}^{bb'}(\mathbf{x}_1, \mathbf{x}_2) = w_{j_1} G_{j_1j_2}^b(\mathbf{x}_1, \mathbf{x}_2) G_{j_1j_2}^{b'}(\mathbf{x}_1, \mathbf{x}_2) w_{j_2} \\ + w_{j_1} \sum_j \int d\mathbf{x} G_{j_1j}^b(\mathbf{x}_1, \mathbf{x}) G_{j_1j}^{b'}(\mathbf{x}_1, \mathbf{x}) \tilde{C}_{jj_2}^{bb'}(\mathbf{x}, \mathbf{x}_2). \quad (5)$$

In the following we use Eqs. (4) and (5) to calculate $\delta\sigma_{\alpha\alpha'}$ for both directions of the magnetic field, perpendicular and parallel to the layers.

III. PERPENDICULAR MAGNETIC FIELD

Consider the case when the field B is directed perpendicular to the layers, $\mathbf{B} = (0, 0, B)$. In the Landau gauge, $\mathbf{A} = (0, Bx, 0)$, we can write the Green's function as

$$G_{j_1j_2}^b(\mathbf{x}_1, \mathbf{x}_2) = \frac{1}{2\pi\ell^2} e^{-i(x_1+x_2)(y_1-y_2)/2\ell^2} e^{-(\mathbf{x}_1-\mathbf{x}_2)^2/4\ell^2} \\ \times \sum_n L_n^0 \left((\mathbf{x}_1 - \mathbf{x}_2)^2/2\ell^2 \right) G_{j_1j_2}^b(n), \quad (6)$$

where $G_{j_1 j_2}^b(n)$ is the averaged Green's function in the Landau-level representation, L_n^0 are the Laguerre polynomials, and $\ell = \sqrt{\hbar/eB}$ the magnetic length. From Eqs. (5) and (6) it follows that the Cooperon may be written as

$$\tilde{C}_{j_1 j_2}^{bb'}(\mathbf{x}_1, \mathbf{x}_2) = e^{-i(x_1+x_2)(y_1-y_2)/\ell^2} C_{j_1 j_2}^{bb'}(|\mathbf{x}_1 - \mathbf{x}_2|), \quad (7)$$

where $C_{j_1 j_2}^{bb'}$ is its translationally invariant part, which is also called Cooperon in the following.

Introducing $C_{jj'}^{bb'}(p)$ as the Fourier transform of $C_{jj'}^{bb'}(x)$, we obtain

$$\begin{aligned} C_{j_1 j_2}^{bb'}(p) &= w_{j_1} \Lambda_{j_1 j_2}^{bb'}(p) w_{j_2} + w_{j_1} \sum_{p', j} \int d\mathbf{x} e^{\frac{i}{\hbar}(\mathbf{p}' - \mathbf{p}) \cdot \mathbf{x}} \\ &\quad \times \Lambda_{j_1 j}^{bb'} \left([(p'_x - \hbar y/\ell^2)^2 + (p'_y + \hbar x/\ell^2)^2]^{1/2} \right) C_{jj_2}^{bb'}(p'), \end{aligned} \quad (8)$$

where $\Lambda_{j_1 j_2}^{bb'}(p)$ is the Fourier transform of the translationally invariant part of the product $G_{j_1 j_2}^b(\mathbf{x}_1, \mathbf{x}_2) G_{j_1 j_2}^{b'}(\mathbf{x}_1, \mathbf{x}_2)$. In the Landau-level representation it can be expressed as

$$\Lambda_{jj'}^{bb'}(p) = \frac{1}{2\pi\ell^2} \sum_{nn'} (-1)^{n+n'} \exp(-u) L_n^{n-n'}(u) L_{n'}^{n'-n}(u) G_{jj'}^b(n) G_{jj'}^{b'}(n'), \quad (9)$$

where $u = p^2 \ell^2 / 2\hbar^2$. Below we consider very weak fields B , $\ell^2 \gg (v_{Fj} \tau_j)^2$, where v_{Fj} and τ_j are, respectively, the Fermi velocities and elastic scattering times in the layers. In this *diffusion limit* we can expand $\Lambda_{jj'}^{bb'}(\dots)$ of Eq. (8) in series of $\hbar x/\ell^2$ and $\hbar y/\ell^2$. From Eq. (8) we obtain a set of differential equations

$$C_{j_1 j_2}^{bb'}(p) = w_{j_1} \Lambda_{j_1 j_2}^{bb'}(p) w_{j_2} + w_{j_1} \sum_j \left[\Lambda_{j_1 j}^{bb'}(p) C_{jj_2}^{bb'}(p) - \frac{\hbar^4}{2\ell^4} \frac{d^2 \Lambda_{j_1 j}^{bb'}(p)}{dp^2} \frac{\partial^2}{\partial \mathbf{p}^2} C_{jj_2}^{bb'}(p) \right]. \quad (10)$$

In the diffusion limit we can also neglect the B dependence of $\Lambda_{j_1 j_2}^{bb'}(p)$, using the expression

$$\Lambda_{j_1 j_2}^{bb'}(p) = \sum_{\mathbf{q}} G_{j_1 j_2}^b(\mathbf{p}/2 - \mathbf{q}) G_{j_1 j_2}^{b'}(\mathbf{p}/2 + \mathbf{q}), \quad (11)$$

where $G_{j_1 j_2}^b(\mathbf{p})$ are the matrix elements of the Green's function

$$\hat{G}^{R,A}(\mathbf{p}) = \left[E_F - \frac{p^2}{2m} - \hat{h} \pm \hat{P}_l \frac{i\hbar}{2} \left(\frac{1}{\tau_l} + \frac{1}{\tau_{\phi l}} \right) \pm \hat{P}_r \frac{i\hbar}{2} \left(\frac{1}{\tau_r} + \frac{1}{\tau_{\phi r}} \right) \right]^{-1} \quad (12)$$

describing the double-layer system in the absence of the magnetic field. The Fermi energy is measured from the center between the two levels of the double quantum well, the elastic scattering times are introduced as $\tau_j = \hbar^3/mw_j$, and $\tau_{\phi j}$ are the phenomenologically introduced inelastic scattering times.

In the weak coupling limit

$$\frac{1}{\tau_t} = \frac{2(T/\hbar)^2 \tau}{1 + (\Delta\tau/\hbar)^2} \ll \frac{1}{\tau}, \quad (13)$$

where $\tau = 2\tau_l\tau_r/(\tau_l + \tau_r)$ is the average elastic scattering time and τ_t the tunneling time. A calculation of $\Lambda_{j_1 j_2}^{bb'}(p)$ in the limit (13) gives

$$\Lambda_{jj}^{RA}(p) \simeq \frac{1}{w_j} \left(1 - \frac{\tau_j}{\tau_{\varphi j}} - D_j \tau_j \left(\frac{p}{\hbar} \right)^2 - \frac{\tau_j}{\tau_t} \right) \quad (14)$$

and

$$\Lambda_{lr}^{RA}(p) = \Lambda_{rl}^{RA}(p) \simeq \frac{\tau_l + \tau_r}{(w_l + w_r)\tau_t}. \quad (15)$$

In Eq. (14) we introduced the 2D diffusion coefficients in the layers $D_j = v_{Fj}^2 \tau_j / 2$. $\Lambda_{jj'}^{AR}(p)$ is given by Eqs. (14) and (15) as well while $\Lambda_{jj'}^{RR}(p)$ and $\Lambda_{jj'}^{AA}(p)$ are small and can be neglected.

A substitution of Eqs. (14) and (15) into Eq. (10) leads to the following equations

$$-\frac{\hbar^2 D_l \tau_l}{\ell^4} \frac{\partial^2}{\partial \mathbf{p}^2} C_{ll}^{RA}(p) + \left(\frac{\tau_l}{\tau_{\varphi l}} + D_l \tau_l \left(\frac{p}{\hbar} \right)^2 + \frac{\tau_l}{\tau_t} \right) C_{ll}^{RA}(p) - \frac{\tau_r}{\tau_t} C_{rl}^{RA}(p) = w_l, \quad (16)$$

$$-\frac{\hbar^2 D_r \tau_r}{\ell^4} \frac{\partial^2}{\partial \mathbf{p}^2} C_{rl}^{RA}(p) + \left(\frac{\tau_r}{\tau_{\varphi r}} + D_r \tau_r \left(\frac{p}{\hbar} \right)^2 + \frac{\tau_r}{\tau_t} \right) C_{rl}^{RA}(p) - \frac{\tau_l}{\tau_t} C_{ll}^{RA}(p) = 0. \quad (17)$$

$C_{rr}^{RA}(p)$ and $C_{lr}^{RA}(p)$ are given by Eqs. (16) and (17) with the indices l and r interchanged.

Equations (16) and (17) can be diagonalized by the substitution $C_{ll}^{RA}(p) = C_1^l(p) + C_2^l(p)$ and $C_{rl}^{RA}(p) = \lambda_1 C_1^l(p) + \lambda_2 C_2^l(p)$. For $C_k(p)$ ($k=1,2$) we obtain

$$\left[-\frac{\hbar^2}{\ell^4} \frac{\partial^2}{\partial \mathbf{p}^2} + \left(\frac{p}{\hbar} \right)^2 + q_k^2 \right] C_k^l(p) = \frac{w_l}{\tau_l D_l} A_k, \quad (18)$$

where

$$q_{1,2}^2 = (s_l + s_r) / 2 \pm S / 2, \quad A_{1,2} = 1/2 \pm (s_l - s_r) / 2S. \quad (19)$$

Here $s_j = (D_j \tau_{\varphi j})^{-1} + (D_j \tau_t)^{-1}$, $s_t^2 = (D_l D_r \tau_t^2)^{-1}$, and $S = [(s_l - s_r)^2 + 4s_t^2]^{1/2}$. Equation (18) is analogous to that for the Green's function of a two-dimensional harmonic oscillator and its solution is obtained in a straightforward way. The result is

$$C_l^{RA}(p) = 2 \frac{w_l}{\tau_l D_l} \sum_n (-1)^n e^{-u} L_n^0(2u) \left[\frac{A_1}{(2/\ell^2)(2n+1) + q_1^2} + \frac{A_2}{(2/\ell^2)(2n+1) + q_2^2} \right]. \quad (20)$$

The expression for $C_{rr}^{RA}(p)$ is given by Eq.(20) with the layer indices interchanged.

Both terms in Eq. (20) contain diffusion poles modified due to tunneling. In the absence of tunneling (uncoupled layers) we obtain the well-known result⁴ for each layer. Now we calculate the weak-localization contribution $\delta\sigma_{\alpha\alpha'}$. In the diffusion limit Eq. (4) gives

$$\begin{aligned} \delta\sigma_{\alpha\alpha'} = \frac{e^2 \hbar}{2\pi m^2 L^2} \sum_{bb'=R,A} (-1)^l \sum_{jj'j_1j_2} \sum_{pp'} p_\alpha p'_{\alpha'} G_{jj_1}^b(\mathbf{p}) G_{j_2j'}^b(\mathbf{p}') \\ \times G_{j'j_1}^{b'}(\mathbf{p}') G_{j_2j}^{b'}(\mathbf{p}) C_{j_1j_2}^{bb'}(|\mathbf{p} + \mathbf{p}'|). \end{aligned} \quad (21)$$

In the limit (13) we should retain only the terms with $j = j' = j_1 = j_2$. The weak-localization contribution is expressed through $C_l^{RA}(p)$ and $C_{rr}^{RA}(p)$. It gives a positive magnetoconductivity $\Delta\sigma = \delta\sigma(B) - \delta\sigma(0)$ as a sum of two parts⁹

$$\frac{\Delta\sigma}{\delta\sigma_0} = f\left(\frac{4}{\ell^2 q_1^2}\right) + f\left(\frac{4}{\ell^2 q_2^2}\right). \quad (22)$$

Here $\delta\sigma_0 = e^2/2\pi^2\hbar$, and $f(x) = \psi(1/2 + 1/x) + \ln x$, where $\psi(x)$ is the digamma function. In the absence of the magnetic field, the weak-localization contribution, within logarithmic accuracy, is given as

$$\delta\sigma(0) = \delta\sigma_0 \ln \left(\frac{\tau_l \tau_r}{\tau_{\phi l} \tau_{\phi r}} + 2 \frac{\tau_l \tau_r}{\tau_t \tau_{\phi}} \right), \quad (23)$$

where we introduced an average inelastic scattering time $\tau_{\phi} = 2\tau_{\phi l} \tau_{\phi r} / (\tau_{\phi l} + \tau_{\phi r})$. It is convenient to analyze the results (22) and (23) in the symmetric case described by $D_l = D_r = D$, $\tau_l = \tau_r$, and $\tau_{\phi l} = \tau_{\phi r}$. In this case Eq. (23) takes the form $\delta\sigma(0) = \delta\sigma_0 [\ln(\tau/\tau_{\phi}) + \ln(\tau/\tau_{\phi} + 2\tau/\tau_t)]$. The first term is the same as in the absence of tunneling while the second one is tunneling-dependent. In the symmetric case Eq. (22) gives

$$\frac{\Delta\sigma}{\delta\sigma_0} = f\left(\frac{B}{B_0}\right) + f\left(\frac{B}{B_0(1 + 2\tau_{\phi}/\tau_t)}\right), \quad (24)$$

where $B_0 = \hbar/4eD\tau_{\phi}$ is the characteristic field. In weak magnetic fields, the magnetoconductivity increases according to a B^2 law. In stronger fields, when the magnetic length

ℓ becomes less than $\sqrt{D\tau_t}$, $\delta\sigma(B)$ loses its dependence on the tunneling and the system behaves like two decoupled layers. In the limit $B \gg B_0$, $B \gg B_0(\tau_\varphi/\tau_t)$ the magnetoconductivity is proportional to $2\delta\sigma_0 \ln B$. For $\tau_t \ll \tau_\varphi$, an intermediate regime exists, $B_0 \ll B \ll B_0(\tau_\varphi/\tau_t)$, in which the magnetoconductivity is proportional to $\delta\sigma_0 \ln(B)$. Figure 1 shows the magnetic-field dependence of the magnetoconductivity described by Eq. (24) for several values of τ_φ/τ_t .

IV. PARALLEL MAGNETIC FIELD

Due to the spatial separation of the layers, a field B applied parallel to them can considerably influence the conductivity of the double-layer system, see, for example, Refs. 18-21. This effect occurs as a result of the modification of the electron energy spectrum of the coupled layers by the field B . However, under the condition $\tau_t \gg \tau$ the coherent tunnel coupling is suppressed by the elastic scattering and the effect disappears. In contrast, the influence of this in-plane field B on the weak-localization part of the conductivity should exist as long as $\tau_t < \tau_\varphi$; the corresponding characteristic field B_1 has to be much smaller. An assessment of this influence is given below in the limit (13).

The parallel field renders the electron Green's function anisotropic. For $\mathbf{B} = (0, B, 0)$ we choose $\mathbf{A} = (B(z - z_0), 0, 0)$ with $z_0 = (\langle l|z|l\rangle + \langle r|z|r\rangle)/2$ and obtain^{19,20}

$$\hat{G}^{R,A}(\mathbf{p}) = \left[E_F - \frac{p^2}{2m} - \frac{\Delta_{p_x}}{2} \hat{\sigma}_z - T \hat{\sigma}_x \pm \hat{P}_l \frac{i\hbar}{2} \left(\frac{1}{\tau_l} + \frac{1}{\tau_{\varphi l}} \right) \pm \hat{P}_r \frac{i\hbar}{2} \left(\frac{1}{\tau_r} + \frac{1}{\tau_{\varphi r}} \right) \right]^{-1}, \quad (25)$$

where $\Delta_{p_x} = \Delta - \omega_c Z p_x + \delta_B$, $\omega_c = eB/m$ is the cyclotron frequency, $Z = \langle r|z|r\rangle - \langle l|z|l\rangle$ is the interlayer distance, and $\delta_B \sim B^2$ is a small field-dependent correction to the level splitting which can be neglected for small B .

Using Eq. (25) we can calculate $\Lambda_{jj'}^{bb'}(\mathbf{p})$ from Eq. (11). In contrast to the previous section, $\Lambda_{jj'}^{bb'}(\mathbf{p})$ is now anisotropic. In the limit $\ell^2 \gg Z v_{Fj} \tau_j$ instead of Eq. (14) we have

$$\Lambda_{jj}^{RA}(\mathbf{p}) \simeq \frac{1}{w_j} \left(1 - \frac{\tau_j}{\tau_{\varphi j}} - D_j \tau_j [(p_x \mp p_B)^2 + p_y^2] / \hbar^2 - \frac{\tau_j}{\tau_t} \right), \quad (26)$$

where $p_B = m\omega_c Z = eBZ$, and the upper (lower) sign stands for $j = l$ ($j = r$). Equation (15) remains unchanged. The Bethe-Salpeter equation for the Cooperon now reduces to a set of linear algebraic equations

$$C_{j_1 j_2}^{bb'}(\mathbf{p}) = w_{j_1} \Lambda_{j_1 j_2}^{bb'}(\mathbf{p}) w_{j_2} + w_{j_1} \sum_j \Lambda_{j_1 j}^{bb'}(\mathbf{p}) C_{j j_2}^{bb'}(\mathbf{p}) \quad (27)$$

whose solution is straightforward. A calculation of $\delta\sigma_{\alpha\alpha'}$ can be done according to Eq. (21), with $C_{j_1 j_2}^{bb'}(|\mathbf{p} + \mathbf{p}'|)$ replaced by $C_{j_1 j_2}^{bb'}(\mathbf{p} + \mathbf{p}')$ found from Eq. (27). Since $\tau_t \gg \tau$ holds, we again put $j = j' = j_1 = j_2$ and finally obtain

$$\Delta\sigma = \Delta\sigma_{sat} - \delta\sigma_0 \sum_{j=l,r} \int_0^\infty dx \frac{s_t^2}{(x + s_j)\sqrt{R_j(x)}} \quad , \quad (28)$$

$$\Delta\sigma_{sat} = \delta\sigma_0 \ln \left[\left(1 + \frac{\tau_{\varphi l}}{\tau_t}\right) \left(1 + \frac{\tau_{\varphi r}}{\tau_t}\right) \middle/ \left(1 + \frac{\tau_{\varphi l} + \tau_{\varphi r}}{\tau_t}\right) \right] \quad (29)$$

where $x = (p/\hbar)^2$ and $R_j(x)$ are the fourth-order polynomials defined by

$$\begin{aligned} R_l(x) = & x^4 + 2(s_l + s_r - x_B)x^3 + [(s_l + s_r)^2 + 2(s_l s_r - s_t^2) + 2x_B(s_r - 2s_l) + x_B^2]x^2 \\ & + 2[(s_l + s_r)(s_l s_r - s_t^2) + x_B(2s_l s_r - s_l^2 - s_t^2) + x_B^2 s_l]x + [s_l s_r - s_t^2 + x_B s_l]^2, \end{aligned} \quad (30)$$

with $x_B = (2p_B/\hbar)^2$. The result for $R_r(x)$ is given by Eq. (30) with the layer indices interchanged. Although the field B induces an anisotropy in the Green's functions, the localization correction $\delta\sigma(B)$ is isotropic because the main contribution in Eq. (21) comes from $|\mathbf{p}| \simeq |\mathbf{p}'| \simeq mv_{Fj}$.

Equations (28)-(30) show that in the weak-field region $B \ll B_1$, where $B_1 = \hbar/eZ\sqrt{D\tau_\varphi}$ and $D = 2D_l D_r / (D_l + D_r)$ is the average diffusion coefficient, the magnetoconductivity follows a B^2 law:

$$\frac{\Delta\sigma}{\delta\sigma_0} = \left(\frac{2s_t e Z B}{\hbar S} \right)^2 \left[\frac{s_l + s_r}{s_l s_r - s_t^2} - \frac{2}{S} \ln \left(\frac{s_l + s_r + S}{s_l + s_r - S} \right) \right]. \quad (31)$$

At $\tau_t \ll \tau_{\varphi j}$ we obtain $\Delta\sigma/\delta\sigma_0 = (B/B_1)^2$. In the opposite limit, a simple expression for the magnetoconductivity can be obtained in the symmetric case, $\Delta\sigma/\delta\sigma_0 = \frac{4}{3}(\tau_\varphi/\tau_t)^2(B/B_1)^2$;

it shows a substantial suppression of the magnetoconductivity as a result of decreasing tunneling probability.

With the increase of B , the B -dependence becomes weaker. For $B \gg B_1$ and $B^2 \gg B_1^2 \tau_\varphi / \tau_t$, the integral in Eq. (28) can be neglected and the magnetoconductivity is saturated and equal to $\Delta\sigma_{sat}$ defined by Eq. (29). For $\tau_\varphi / \tau_t \ll 1$ the saturated value goes to zero. Recently, a saturation behavior of the weak-localization contribution in parallel magnetic fields has been theoretically found for superlattices¹⁵.

When the condition $\tau_t \ll \tau_\varphi$ holds, one can analytically evaluate the magnetoconductivity for $B^2 \ll B_1^2 \tau_\varphi / \tau_t$; the result is

$$\Delta\sigma = \delta\sigma_0 \ln[1 + (B/B_1)^2]. \quad (32)$$

It shows that in the intermediate region $B_1^2 \ll B^2 \ll B_1^2 \tau_\varphi / \tau_t$, the magnetoconductivity follows a logarithmic law. In Fig. 2 we demonstrate a transition from a B^2 -behavior at weak fields to the saturation at stronger fields for several values of the ratio τ_t / τ_φ .

The tunneling rate $1/\tau_t$ can be varied by applying a transverse voltage which changes the level splitting Δ ¹⁷. In the case under consideration $E_F \gg \hbar/\tau$, a relatively small variation of Δ has no considerable influence on the electron densities in the wells but can dramatically modify the tunneling rate. Fig. 3 shows the Δ -dependence of $\delta\sigma(B) - \delta\sigma(0)|_{\Delta=0}$ for several values of the magnetic field, for both *parallel* (solid) and *perpendicular* (dashed lines) fields; the thick solid line is the result for $B = 0$. The curves have a typical resonance-like behavior that is affected differently by the two field orientations. An increase of Δ always leads to a decrease of the conductivity, because in this way the tunneling is suppressed and, therefore, the interference is increased. The perpendicular magnetic field tends to smoothen this effect because it suppresses the dependence of the weak-localization part of the conductivity on tunneling, see Sec. III. On the other hand, the parallel field tends to strengthen the tunneling dependence of the weak-localization part: in the saturation regime, cf. Fig. 2, this dependence is the strongest.

Above we calculated the magnetoconductivity in the weak-tunneling regime. Below we

evaluate it again in the regime of coherent tunnel coupling.

V. COHERENT TUNNELING REGIME

The aim of this section is to study the weak localization effects at sufficiently strong, coherent tunnel coupling, described by $\tau_t \sim \tau$ or even $\tau_t \ll \tau$. In these conditions one always has $\tau_t \ll \tau_\varphi$, which means that there is no competition between the tunneling and inelastic scattering processes. As a result, instead of two diffusion poles, see Eq. (20), the expression for the Cooperon contains just one pole as for a single-layer system. However, the properties of this pole are somewhat different than those in case of a single 2D layer and require a separate consideration.

Below we assume that E_F is large in comparison with T and Δ . Introducing a single Fermi velocity v_F for both layers, we write average diffusion coefficient as $D = v_F^2 \tau / 2$. The calculation of the Cooperon according to Eqs. (11), (25), and (27) gives

$$C_{jj'}(\mathbf{p}) = \frac{w_j w_{j'}}{w_l + w_r} \left[\frac{\tau}{\tau_\varphi} + \frac{D(\Delta)\tau}{\hbar^2} (p^2 + r(\Delta)p_B^2 + 2\mu r(\Delta)p_B p_x) \right]^{-1}. \quad (33)$$

The inelastic scattering time enters the diffusion pole only as an average. On the other hand, the Cooperon depends on the asymmetry of the elastic scattering described by the parameter $\mu = (\tau_r - \tau_l)/(\tau_r + \tau_l)$. In Eq. (33) we have also introduced a Δ -dependent diffusion coefficient according to

$$D(\Delta) = \frac{D}{1 - \mu^2 r(\Delta)}, \quad r(\Delta) = \frac{\Delta^2 + (\hbar/\tau)^2}{\Delta^2 + 4T^2 + (\hbar/\tau)^2}. \quad (34)$$

Note that $D(\Delta)$ differs from D only if the elastic scattering is asymmetric.

If there is no parallel magnetic field ($p_B = 0$), Eq. (33) has the same form as the Cooperon of a single-layer system. Therefore, in the diffusion regime Eq. (33) with a substitution $p^2 \rightarrow 4\hbar e B(n + 1/2)$ can be directly used to calculate the magnetconductivity in a perpendicular magnetic field B . Using Eq. (21), we obtain, in analogy with the single-layer case,

$$\Delta\sigma = \delta\sigma_0 f\left(\frac{4eD(\Delta)B\tau_\varphi}{\hbar}\right), \quad (35)$$

and, within the logarithmic accuracy, $\delta\sigma(0) = \delta\sigma_0 \ln(\tau/\tau_\varphi)$. The only difference between Eq. (35) and the well-known expression for a single-layer 2D system is the replacement of D in the latter by $D(\Delta)$. The physical meaning of this change is clear and easily understood in terms of the resistance resonance phenomenon^{22,23}, see also Ref. 17. In the corresponding theory^{22,23} the factor $1/[1 - \mu^2 r(\Delta)]$ describes the Δ -dependence of the conductivity and of the diffusion coefficient D of the double quantum wells with asymmetric scattering. With the increase of $|\Delta|$, D increases and leads to an increase of the magnetoconductivity $\Delta\sigma$.

Now we consider the case of a parallel magnetic field. Using Eqs. (33) and (21), we obtain

$$\Delta\sigma = \delta\sigma_0 \ln \left[1 + r(\Delta)(B/B_1)^2 \right]. \quad (36)$$

The magnetoconductivity described by Eq. (36) does not depend on the scattering asymmetry. On the other hand, its dependence on Δ has the same sign as in case of perpendicular field: when Δ increases, $r(\Delta)$ goes to unity and $\Delta\sigma$ increases. The behavior of the magnetoconductivity described by Eqs. (35) and (36) is illustrated in Fig. 4.

The results for magnetoconductivity described in this section are valid for $\tau_t \ll \tau_\varphi$ under conditions $D\tau_t eB/\hbar \ll 1$ for perpendicular field B and $D\tau_t (eZB/\hbar)^2 \ll 1$ for parallel field B . In the limit (13), when $r(\Delta) = 1$, Eq. (35) is equivalent to Eq. (22) written at $\tau_t \ll \tau_\varphi$ and $D\tau_t eB/\hbar \ll 1$, while Eq. (36) is equivalent to Eq. (32).

VI. DISCUSSION

We have investigated the influence of the tunnel coupling between two 2D layers on the weak-localization-induced magnetoconductivity. This coupling introduces an extra degree of freedom for an electron giving it the possibility to tunnel between the layers and, therefore, it reduces the interference effects. As a result, the weak-localization contribution is reduced

as the tunneling rate $1/\tau_t$ overcomes the inelastic scattering rate. In particular, it leads to the weakening of the magnetoresistance in the perpendicular magnetic field, see Sec. III.

The results described in Sec. III are similar to those obtained in Ref. 9 for two thin metallic films divided by a barrier if one equals τ_t to the tunneling times τ_{12} and τ_{21} of Ref. 9. This is not surprising. When the inelastic scattering lengths are small in comparison to the film widths, the diffusion of the electrons in such a system proceeds in the same way as in coupled 2D layers. A characteristic feature of the double quantum well case, as opposed to the case of thin films, is the strong resonance dependence of the tunneling time τ_t , cf. Eq. (13), on the energy-level splitting Δ . The latter can be easily controlled by external gates enclosing the double quantum wells. This opens a new way to examine the weak-localization phenomena by measuring the Δ -dependence of the conductivity, see, for example, Fig. 3, in addition to the B dependence. The conductivity, due to its weak-localization part, is maximal when the tunneling resonance condition $\Delta = 0$ holds (this can be called "delocalisation resonance"), while an increase of Δ increases the interference and leads to a decrease of the conductivity down to its value for uncoupled layers. On the other hand, if the scattering times in the layers are different, the main part of the conductivity will show the opposite effect (the resistance resonance¹⁷). Although the relative size of the resistance resonance would be small due to the parameter τ/τ_t , it can obscure the delocalization resonance. Therefore, the samples with symmetric scattering are preferable for probing the interference corrections.

In Sec. IV we studied the magnetoconductivity in a parallel magnetic field. Since this magnetoconductivity can exist only in the presence of the tunnel coupling, it becomes more pronounced as the tunneling rate overcomes the inelastic scattering rate. Although at very small B both parallel and perpendicular fields give B^2 -corrections to the magnetoconductivity, at higher fields the behavior becomes completely different. When the *perpendicular* field is larger than both B_0 and $B_0\tau_\varphi/\tau_t$, the weak-localization contribution logarithmically increases with B and does not depend on tunneling. When the *parallel* field is larger than

both B_1 and $B_1\sqrt{\tau_\varphi/\tau_t}$, $\delta\sigma(B)$ becomes saturated, i.e., it loses its dependence on B but not that on tunneling. Since $(v_F/Z)\sqrt{\tau_\varphi\tau} \gg 1$ holds, the characteristic parallel field B_1 is much larger than the characteristic perpendicular field B_0 .

With an increase of Δ both $\delta\sigma(B)$ and $\Delta\sigma$ in a parallel magnetic field decrease. However, in the case of coherent tunnel coupling (Sec. V) the behavior of the magnetoconductivity $\Delta\sigma$ versus Δ is opposite: an increase of Δ increases $\Delta\sigma$. A transition between these two kinds of behavior can be explained as follows. When the tunnel coupling becomes so strong that $D\tau_t(eBZ/\hbar)^2 \ll 1$, a change of τ_t with Δ no longer modifies the magnetic-field suppression of the interference, see Sec. IV. With a further increase of the tunneling rate, when the latter overcomes the elastic scattering rate, coherent coupling effects become important. Instead of the states localized in the wells, one has a pair of hybridized states, which are well-defined in the limit of $2T \gg \hbar/\tau$. At $\Delta = 0$ the electron density in both these states is distributed equally among the wells, and the parallel magnetic field cannot reduce the interference in the way described in the Introduction. The magnetoconductivity is zero, which is given also by Eq. (36) at $2T \gg \hbar/\tau$ and $\Delta = 0$. At $\Delta \neq 0$ the symmetry is broken. The two states are mostly localized in different wells and the parallel magnetic field can reduce the interference because the transitions of electrons between these states are possible. In conclusion, the magnetoconductivity increases with an increase of Δ .

Let us briefly discuss the main approximations used in this paper. Since we neglected the electron-electron interaction, which also leads to quantum corrections to the conductivity, the theory is applicable at temperatures considerably lower than $\hbar/\tau_\varphi$ ²⁴. We also neglected the possibility of spin-flip scattering, assuming that the relevant scattering time is larger than τ_φ . The assumption of the δ -correlated scattering does not lead to principal changes. For example, if one takes into account the interlayer correlation of the scattering amplitudes, one has to replace only $1/\tau$ in Eq. (13) by $1/\tau - 1/\tau_{lr}$, where $\tau_{lr} = \hbar^3/mw_{lr}$.

Throughout the paper we calculated the total, i.e. summed over both layers, in-plane conductivity of the double-layer system. Experimentally it corresponds to the double quan-

tum wells with common contacts to the layers. The case of independently contacted layers does not require a separate consideration for the following reason. Since the system is assumed macroscopic, its in-plane size should substantially exceed the inelastic scattering length $v_F\tau_\varphi$. On the other hand, the tunnel coupling manifests itself in weak-localization phenomena under the condition $\tau_\varphi > \tau_t$. In such a case a characteristic current redistribution length²⁵ $l_s \sim \sqrt{v_F^2\tau\tau_t}$ is small in comparison to the size of the system, which means that for any case of independent contacting the double-layer system would behave as a system with common contacts.

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FIGURES

FIG. 1. Magnetoconductivity of the double-layer system in a *perpendicular* magnetic field B for symmetric conditions. The curves are marked with the values of the ratio τ_t/τ_φ and $B_0 = \hbar/4eD\tau_\varphi$

FIG. 2. Magnetoconductivity of the double-layer system in a *parallel* magnetic field B for symmetric conditions. The curves are marked as in Fig. 1 and $B_1 = \hbar/eZ\sqrt{D\tau_\varphi}$

FIG. 3. Relative weak-localization correction to the conductivity of the double-layer system as a function of the level splitting Δ for several values of the *parallel* (solid) and *perpendicular* (dashed) magnetic field. It is assumed that $\tau_t/\tau_\varphi = 0.1$ at $\Delta = 0$. The numbers next to the curves show the values of B/B_0 (perpendicular field) and $(B/B_1)^2$ (parallel field).

FIG. 4. Magnetoconductivity of the double-layer system in a coherent tunneling regime for $2T\tau/\hbar = 4$ and $\mu = 0.7$. The solid and dashed lines correspond to parallel and perpendicular field, respectively. The curves are marked with the values of the ratio $\Delta/2T$.

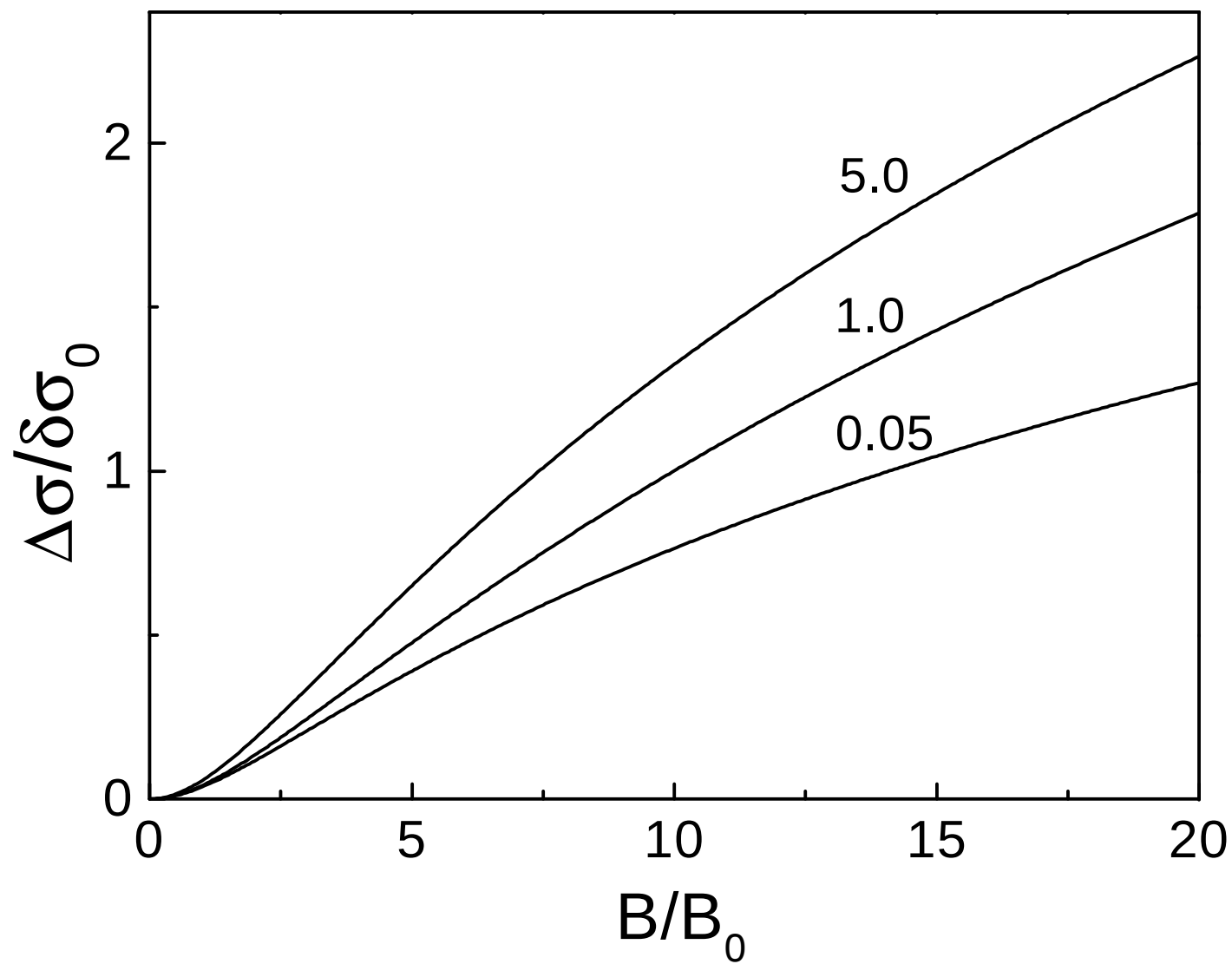


Fig.1 O.E.Raichev and P.Vasilopoulos, "Weak localization..."

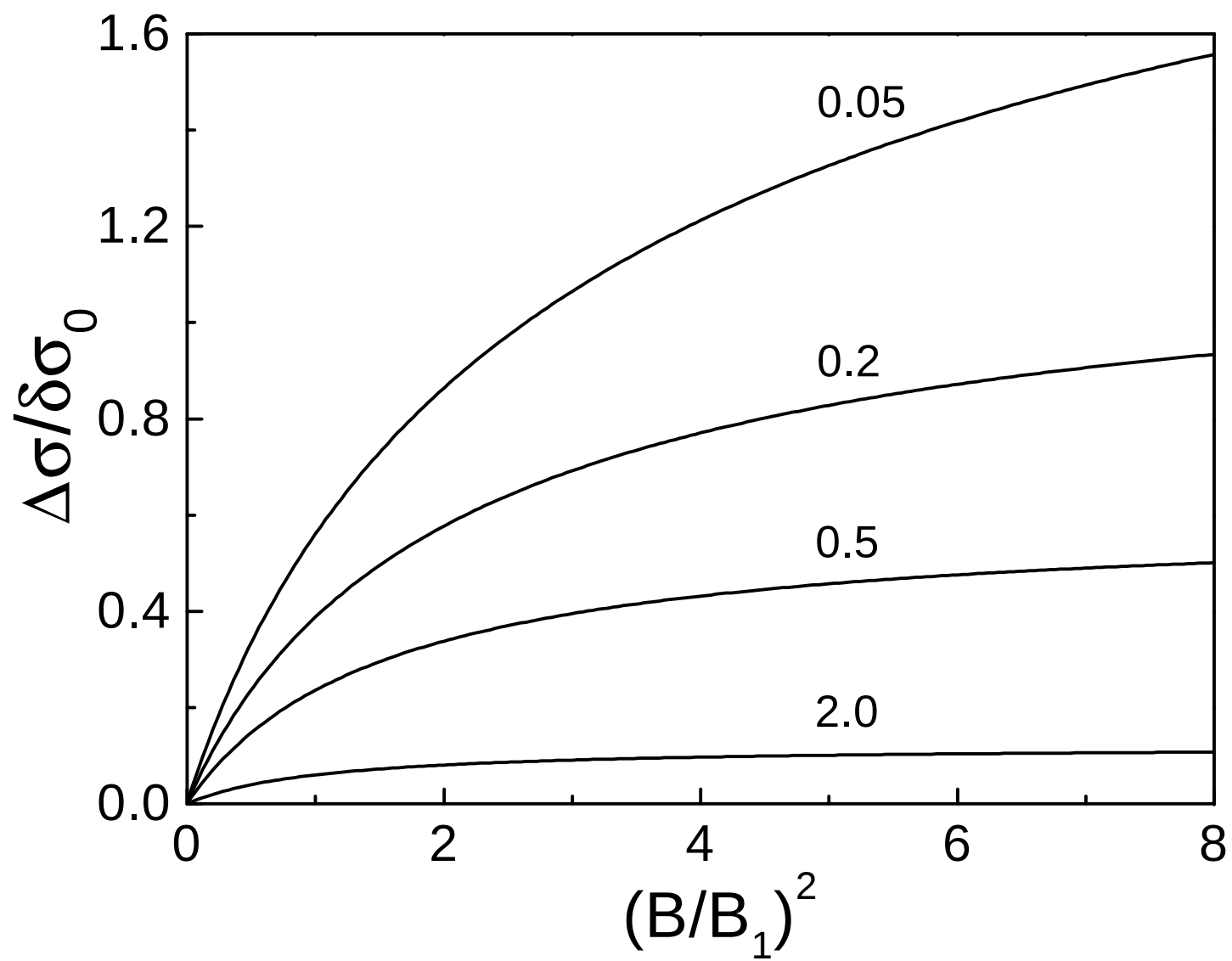


Fig.2 O.E.Raichev and P.Vasilopoulos "Weak localization..."

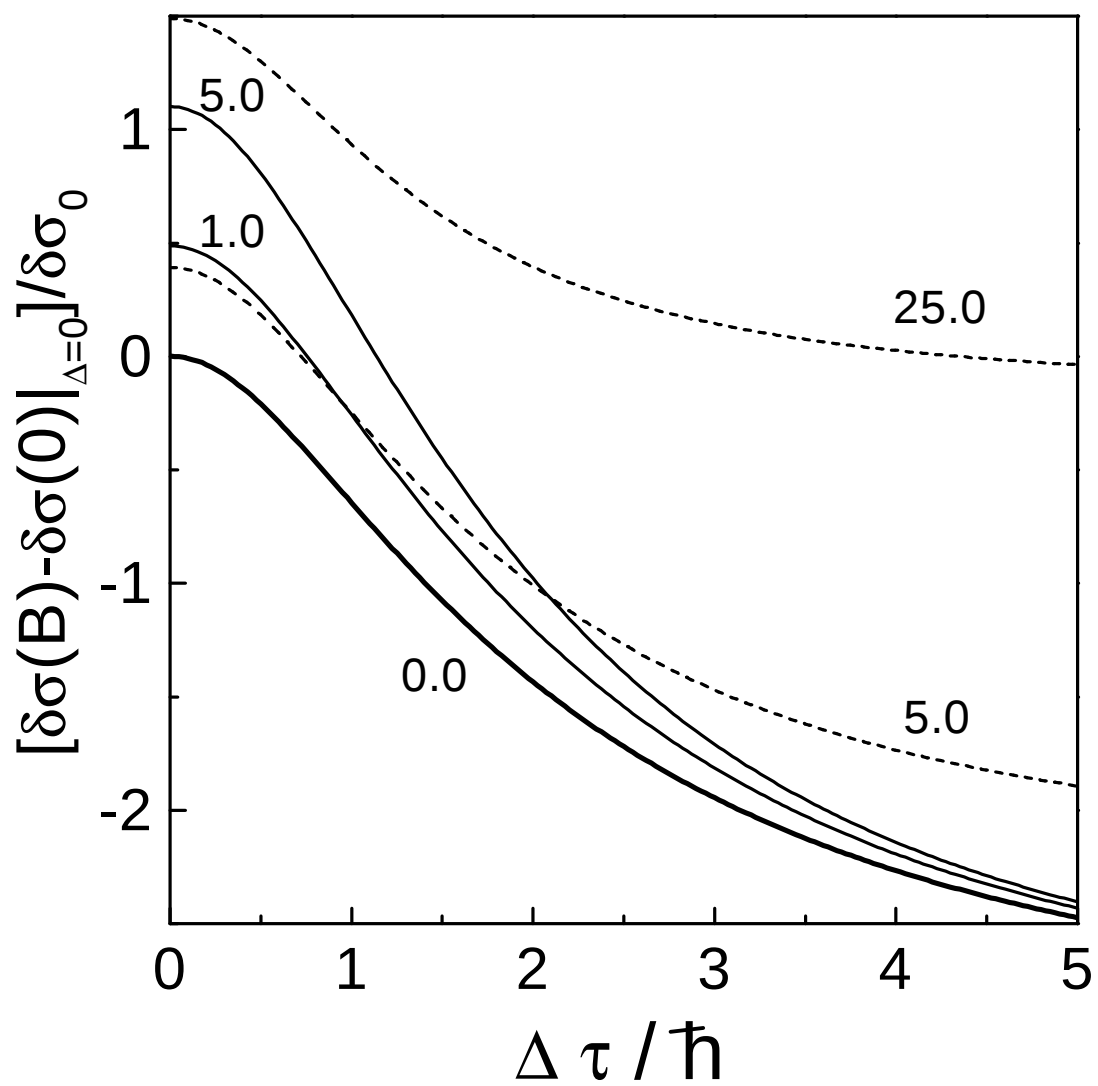


Fig.3 O.E.Raichev and P.Vasilopoulos "Weak localization..."

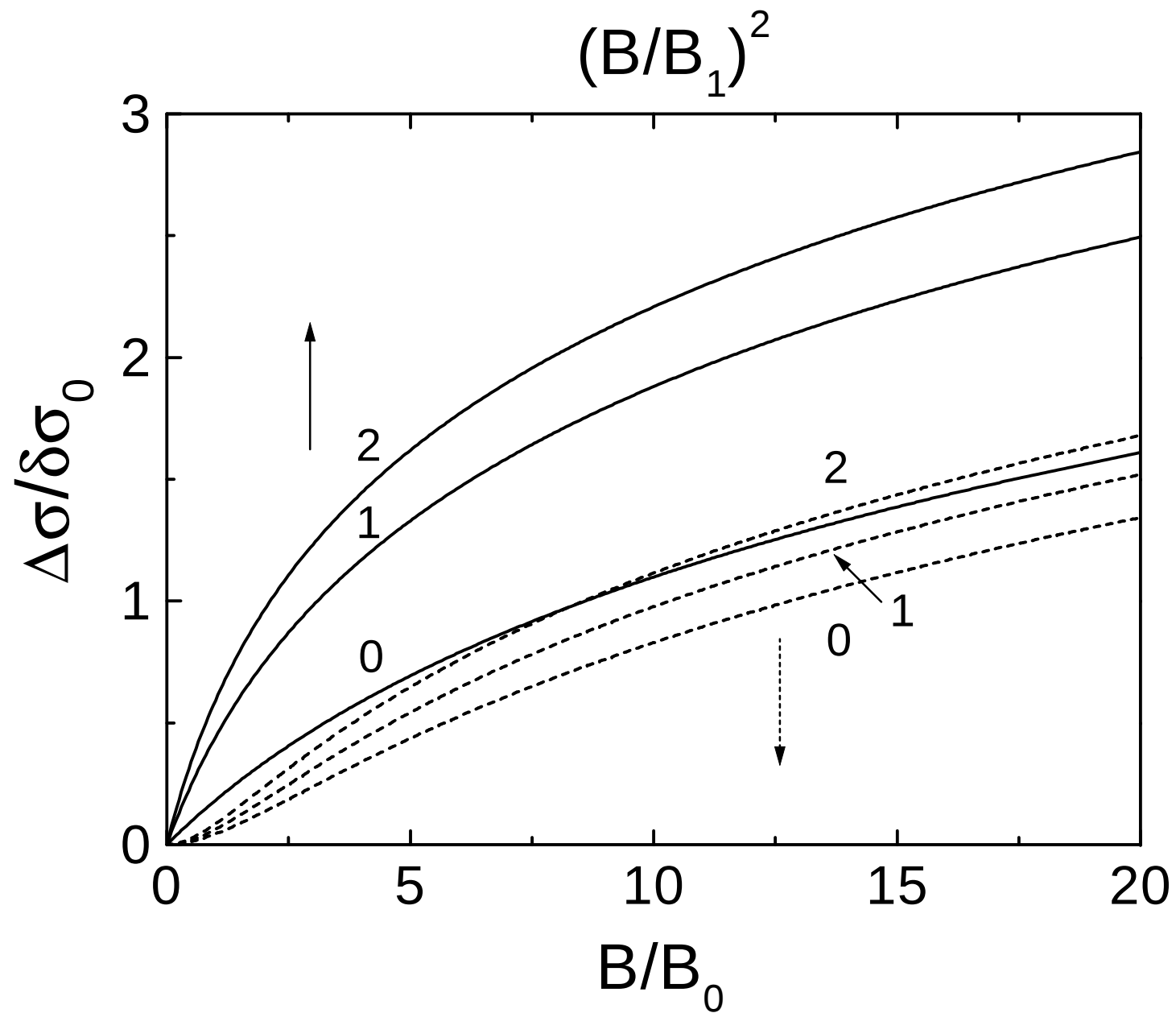


Fig.4 O.E.Raichev and P.Vasilopoulos "Weak localization..."